AutoEtch 790

The AutoEtch 790 has been designed specifically for processes requiring good control over anisotropy including Tungsten etch back applications.
The cathode coupled design enhances ion bombardment with a focus ring to confine the plasma . The 790 is a safe, high throughput vacuum load locked system.

Applications

- **W etch back**
- **Polycide structures**
- Refractory metals etch
- Shallow trench
- Nitride Etch

ichor systems

Typical Results

W etch back

SF_6/He

- W Etch rate > 3000A/min
- Uniformity +/- 15% 3σ
- TiW glue layer to TEOS selectivity 7:1

Typical Results

Nitride Etch

SF_6/O_2

- SiN Etch rate > 1800A/min
- Uniformity +/- 15% 3σ
- Selectivity to oxide 4:1

Typical Results

Shallow trench

CL_2/CCl_4/He

- Si Etch rate 10000A/min
- Uniformity +/- 15% 3σ
- Selectivity to oxide >10:1